

# MXD8546F

X-DPDT Switch for 0.4~3.8G Application

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#### **General Description**

The MXD8546F is a CMOS, Silicon-On-Insulator (SOI) double-pole, double-throw (DPDT) switch. The switch provides high linearity performance, low insertion loss and high isolation.

Switching is controlled by one control voltage, V1. Depending on the logic voltage level applied to this pin, the RF1 and RF2 pins connect to one of the two other RF port pins (RF3 or RF4) through a low insertion loss path, while maintaining a high isolation path to the alternate port. No external DC blocking capacitors are required on the RF path as long as no DC voltage is applied externally.

The MXD8546F DPDT switch is provided in a compact Quad Flat No-Lead (QFN) 2 x 2 mm package. A functional block diagram is shown in Figure 1. The pin configuration and package are shown in Figure 2. Signal pin assignments and functional pin descriptions are provided in Table 1.

## **Applications**

- Simultaneous voice and LTE systems
- Diversity antenna switching

#### **Features**

- Single control voltage input
- Broadband frequency range: 0.4 to 3.8 GHz
- Low insertion loss: 0.45 dB @ 2.7 GHz
- P0.1dB of 38dBm
- No DC blocking capacitors required
- Positive control voltage range: 1.8 to 3.3 V
- Small, QFN (12-pin, 2 x 2 mm) package

## **Functional Block Diagram and Pin Function**

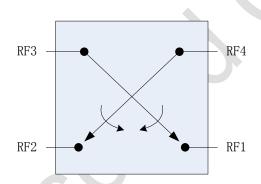


Figure 1. Functional Block Diagram

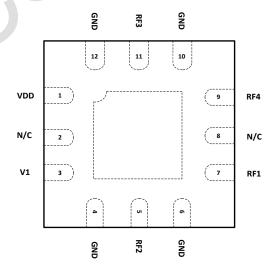


Figure 2. Pin Diagram



## **Application Circuit**

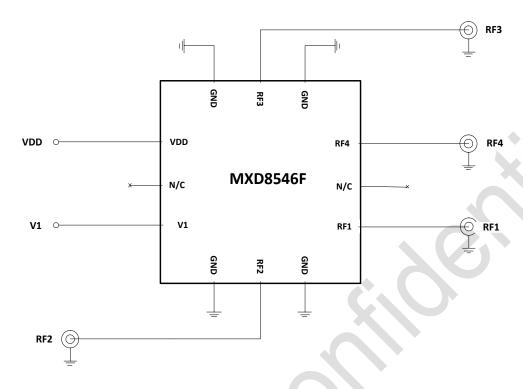


Figure 3. MXD8546F Application Circuit

**Table 1. Pin Description** 

Pin No.	Name	Description	Pin No.	Name	Description
1	VDD	DC power supply	7	RF1	RF port 1
2	N/C	No connection	8	N/C	No connection
3	V1	DC control voltage 1.	9	RF4	RF Port 4
4	GND	Ground.	10	GND	Ground.
5	RF2	RF port 2	11	RF3	RF port 3
6	GND	Ground.	12	GND	Ground.

Note: Bottom ground paddles must be connected to ground.

#### **Truth Table**

Table 2.

V1	State
1	RF3 to RF1,RF4 to RF2
0	RF3 to RF2, RF4 to RF1

Note: "1" = 1.8 to 3.1 V, "0" = -0.20 to +0.45 V; Any state other than described in this Table places the switch into an undefined state.

# **Recommended Operation Range**

#### Table 3.

Parameters	Symbol	Min	Тур	Max	Units
Operation Frequency	f1	0.4	-	3.8	GHz
Power supply	$V_{DD}$	1.8	2.8	3.3	V
Switch Control Voltage High	V <sub>CTL_</sub> H	1.0	1.8	3.3	V
Switch Control Voltage Low	V <sub>CTL_L</sub>	0	0	0.3	V



## **Specifications**

#### **Table 4. Electrical Specifications**

Doromotor	Symbol		pecification		Units	Test Condition	
Parameter	Symbol	Min.	Typical	Max.	Units	rest Condition	
DC Specifications							
Control voltage: Low High	Vctl_l Vctl_h	0 1.0	0 1.8	0.3 3.3	V		
Supply voltage	V <sub>DD</sub>	1.8	2.8	3.3	V		
Supply current	I <sub>DD</sub>		60	85		V <sub>DD</sub> = 2.8 V	
Control current	Ictl		1	5	μA	Vctl= 1.8 V	
RF Specifications							
Insertion loss (RF1/RF2 to RF3/RF4)	IL		0.33 0.40 0.45 0.55		dB dB dB dB	0.7 to 1.0 GHz 1.0 to 2.2 GHz 2.5 to 2.7 GHz 3.4 to 3.8 GHz	
Isolation (RF1/RF2 to RF3/RF4, RF1 to RF2, RF3 to RF4)	ISO	28 24 21 16	31 26 23 18		dB dB dB dB	0.7 to 1.0 GHz 1.0 to 2.2 GHz 2.5 to 2.7 GHz 3.4 to 3.8 GHz	
Input return loss (RF1/RF2 to RF3/RF4)	RL	15	20		dB	0.7 to 3.8 GHz	
0.1 dB Compression Point (RF1/RF2 to RF3/RF4)	P <sub>0.1dB</sub>		+38		dBm	0.7 to 3.8 GHz	
2 <sup>nd</sup> Harmonic (RF1/RF2 to RF3/RF4)	2fo		-100	-83	dBc	fo = 824 to 915 MHz, P <sub>IN</sub> =	
3 <sup>rd</sup> Harmonic(RF1/RF2 to RF3/RF4)	3fo		-95	-83	dBc	+35 dBm	
Switching on time			2	5	μs	50% VCTL to 90% RF	
Switching off time			2	5	μs	50% VCTL to 10% RF	
Startup time			10		μs	Power off state to any RF switch state	

# **Absolute Maximum Ratings**

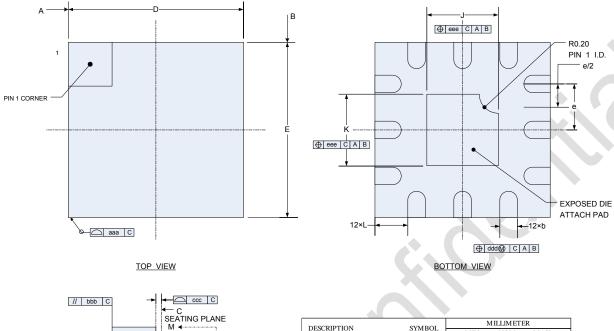
#### Table 5. Maximum ratings

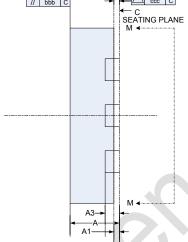
Parameters	Symbol	Minimum	Maximum	Units
Supply voltage	$V_{DD}$	+1.8	+3.3	V
Digital control voltage	Vctl	0	+3.3	V
RF input power	P <sub>IN</sub>		+39	dBm
Operating temperature	T <sub>OP</sub>	-30	+85	°C
Storage temperature	T <sub>STG</sub>	-55	+150	°C
Electrostatic Discharge Human body model (HBM), Class 2 Machine Model (MM), Class B Charged device model (CDM), Class III	ESD_HBM ESD_MM ESD_CDM		2000 200 500	V

**Note:** Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device



# **Package Outline Dimension**





DESCRIPTION		SYMBOL	MILLIMETER			
		SIMBOL	MIN	NOM	MAX	
TOTALTHIC	KNESS	A	0.51	0.55	0.60	
STAND OFF		A1	00.0	0.02	0.05	
L/F THICKNE	ESS	A3	-	0.15 Ref	-	
EAD WIDTH		b	0.15	0.20	0.25	
BODY SIZE	X	D	-	2.00 BSC	-	
BOD1 SIZE	Y	E	-	2.00 BSC	-	
LEAD PITCH		e	0.50 BSC			
EP SIZE	X	J	0.77	0.92	1.02	
EF SIZE	Y	K	0.77	0.92	1.02	
LEAD LENG	TH	L	0.19	0.29	0.39	
PACKAGE EI	OGE TOLERANCE	aaa	0.05			
MOLD FLAT	NESS	bbb	0.10			
COPLANARI	TY	ccc	0.10			
LEAD OFFSE	T	ddd	0.05			
EXPOSED PA	AD OFFSET	eee	0.08			

Figure 4. package outline dimension



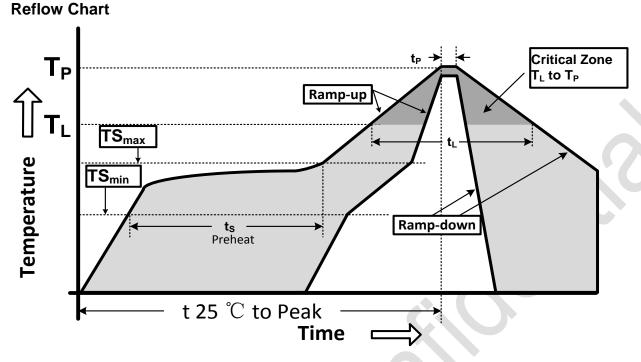


Figure 5. Recommended Lead-Free Reflow Profile

#### **Table 6 Reflow condition**

Profile Parameter	Lead-Free Assembly, Convection, IR/Convection
Ramp-up rate (TS <sub>max</sub> to T <sub>p</sub> )	3°C/second max.
Preheat temperature (TS <sub>min</sub> to TS <sub>max</sub> )	150℃ to 200℃
Preheat time (t <sub>s</sub> )	60 - 180 seconds
Time above TL , 217°C (t <sub>L</sub> )	60 - 150 seconds
Peak temperature (T <sub>p</sub> )	260℃
Time within 5°C of peak temperature(t <sub>p</sub> )	20 - 40 seconds
Ramp-down rate	6°C/second max.
Time 25℃ to peak temperature	8 minutes max.

#### **ESD Sensitivity**

Integrated circuits are ESD sensitive and can be damaged by static electric charge. Proper ESD protection techniques should be used when handling these devices.

## **RoHS Compliant**

This product does not contain lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE), and are considered RoHS compliant.

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